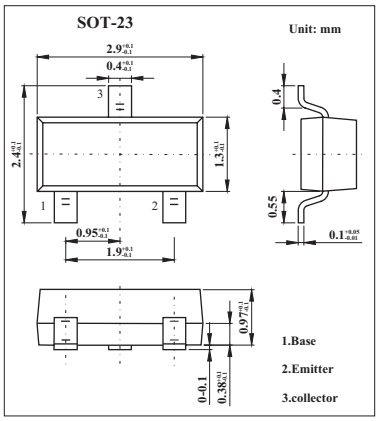
PNP Silicon Epitaxial Transistor

2SA1362



■ Features

- High DC Current Gain
- Low Saturation Voltage
- Suitable for Driver Stage of Small Motor
- Small package.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-15	V
Collector-emitter voltage	V_{CEO}	-15	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-800	mA
Base current	I_B	-160	mA
Collector dissipation	P_C	200	mW
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cut-off current	I_{CBO}	V_{CB} = -15 V, I_E = 0			-100	nA
Emitter cut-off current	I_{EBO}	V_{EB} = -5 V, I_C = 0			-100	nA
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C = -10 mA, I_B = 0	-15			V
DC current gain	h_{FE}	V_{CE} = -1 V, I_C = -100 mA	120		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = -400 mA, I_B = -8 mA			-0.2	V
Base-emitter voltage	V_{BE}	V_{CE} = -1 V, I_C = -10 mA	-0.5		-0.8	V
Transition frequency	f_T	V_{CE} = -5 V, I_C = -10 mA		120		MHz
Collector output capacitance	C_{ob}	V_{CB} = -10 V, I_E = 0, f = 1 MHz		13		pF

■ hFE Classification

Marking	AE	
Rank	Y	G
hFE	120-240	200～400